

P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY

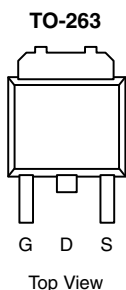
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 40	0.005 at $V_{GS} = - 10$ V	- 110	185 nC

FEATURES

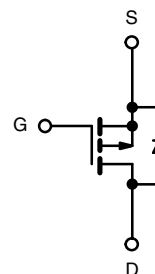
- TrenchFET[®] Power MOSFET



RoHS
COMPLIANT



Drain Connected to Tab



Ordering Information: SUM110P04-05-E3 (Lead (Pb)-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Pulsed Drain Current	I_{DM}	240	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	
Avalanche Current	I_{AS}	75	
Single-Pulse Avalanche Energy	E_{AS}	281	mJ
Maximum Power Dissipation	P_D	$T_C = 25$ °C	W
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	8	10	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	0.33	0.4	

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 10$ s.

d. Maximum under Steady State conditions is 40 °C/W.

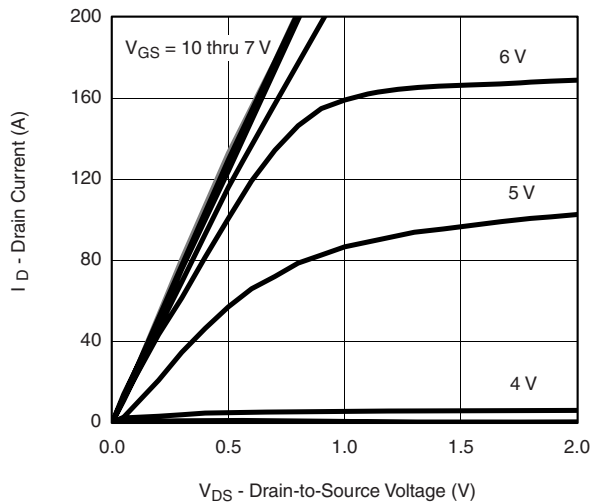
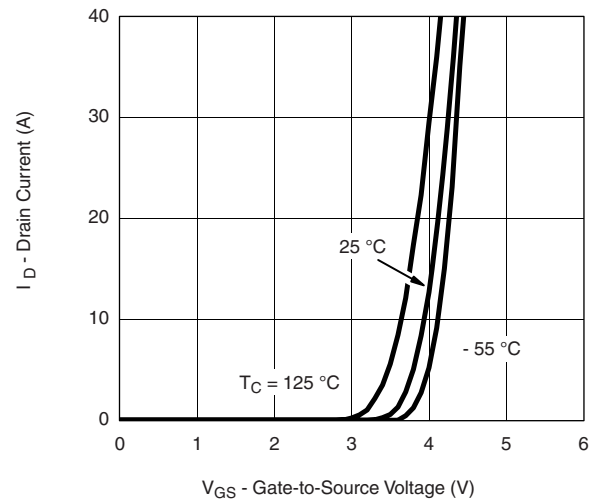
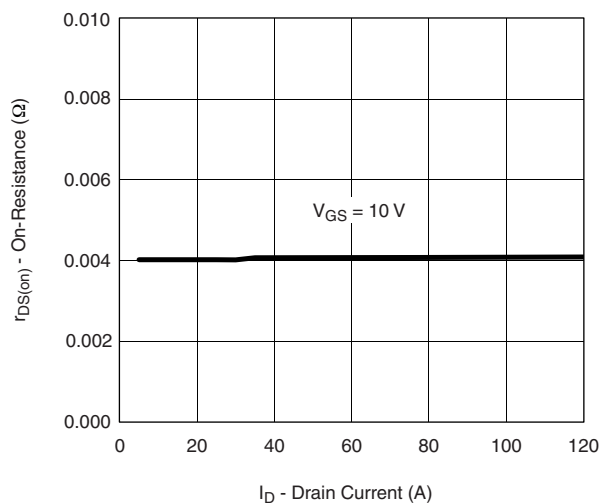
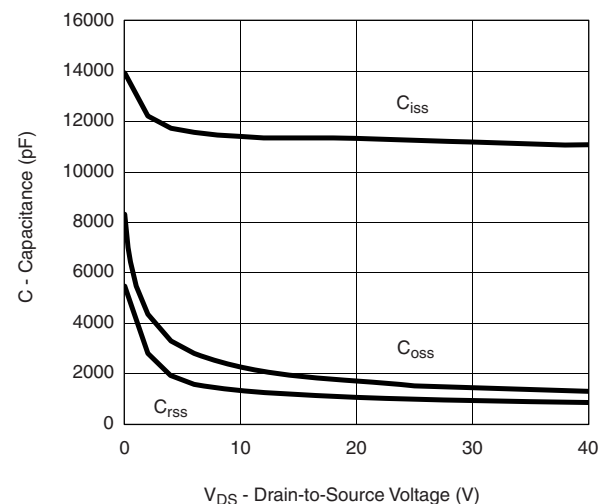
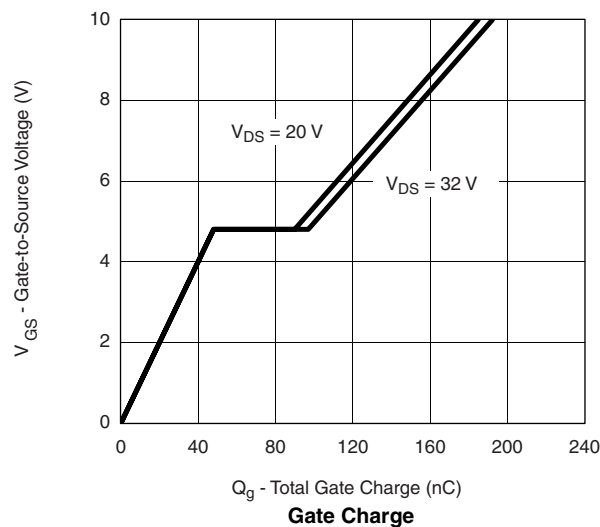
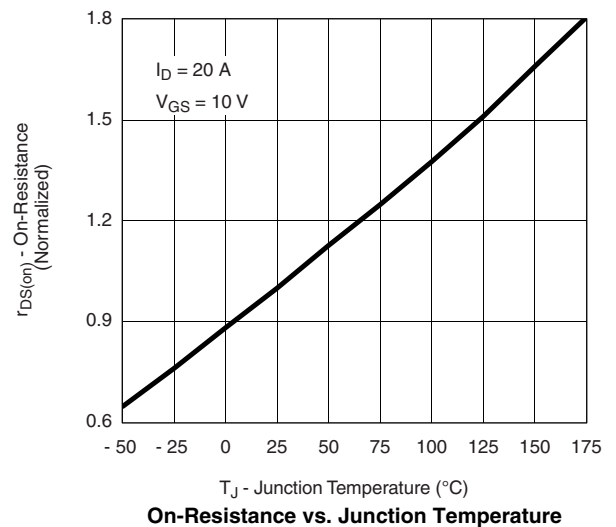
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 40			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 40		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 2	- 3	- 4	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 40 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = - 10 V	- 120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = - 10 V, I _D = - 20 A		0.0041	0.005	Ω
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 20 A		75		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		11300		pF
Output Capacitance	C _{oss}			1510		
Reverse Transfer Capacitance	C _{rss}			1000		
Total Gate Charge	Q _g	V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = - 110 A		185	280	nC
Gate-Source Charge	Q _{gs}			48		
Gate-Drain Charge	Q _{gd}			42		
Gate Resistance	R _g	f = 1 MHz		4.0		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 20 V, R _L = 0.18 Ω I _D ≅ - 110 A, V _{GEN} = - 10 V, R _g = 1 Ω		25	40	ns
Rise Time	t _r			290	440	
Turn-Off Delay Time	t _{d(off)}			110	165	
Fall Time	t _f			35	55	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 110	A
Pulse Diode Forward Current ^a	I _{SM}				- 240	
Body Diode Voltage	V _{SD}	I _S = - 20 A		- 0.8	- 1.5	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 20 A, di/dt = 100 A/μs, T _J = 25 °C		70	105	ns
Body Diode Reverse Recovery Charge	Q _{rr}			130	200	nC
Reverse Recovery Fall Time	t _a			37		ns
Reverse Recovery Rise Time	t _b			33		

Notes:

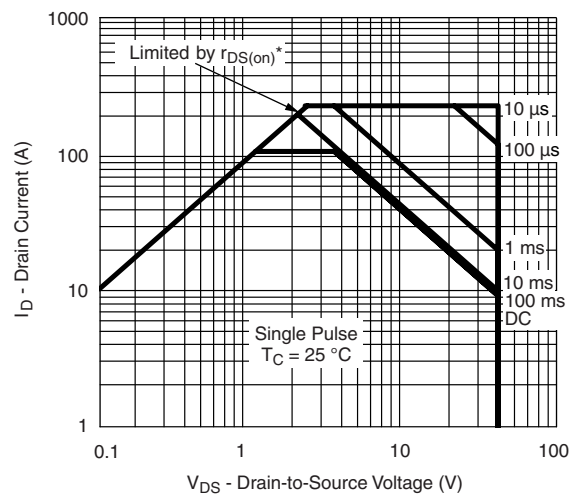
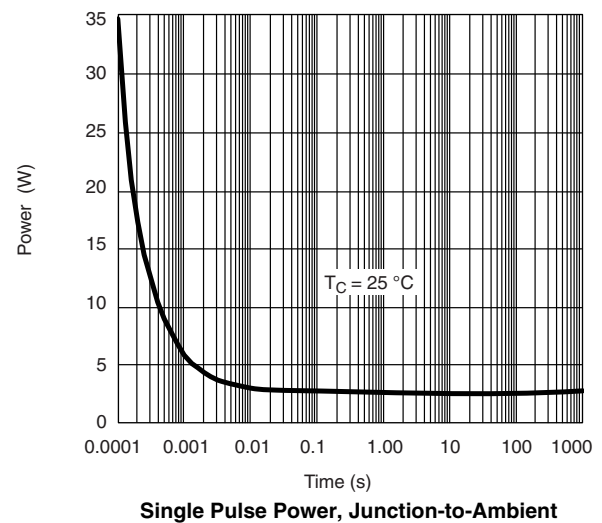
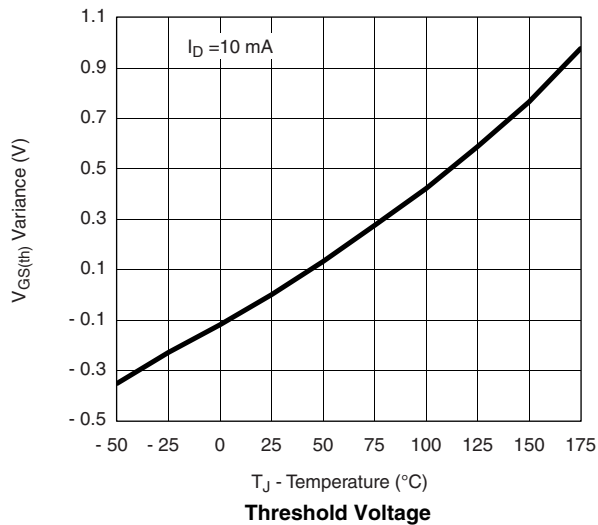
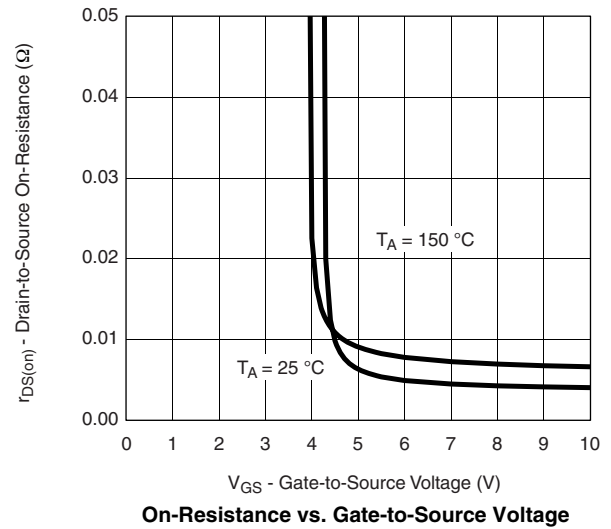
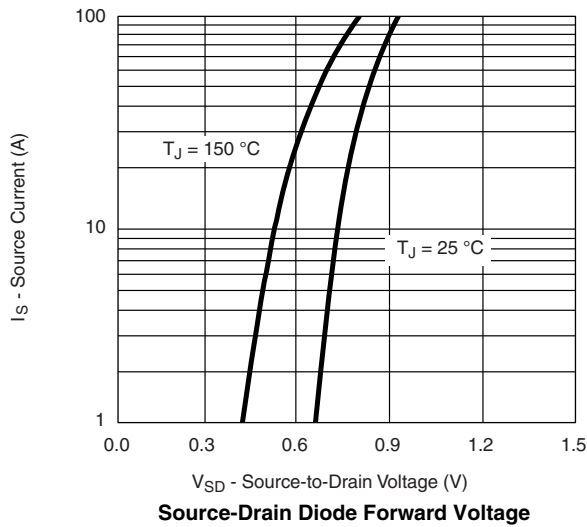
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

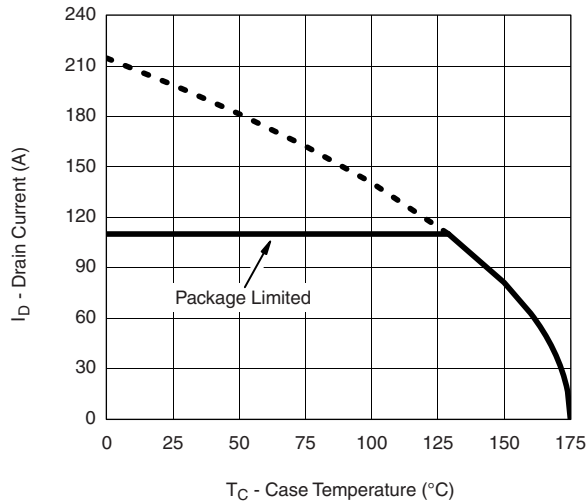
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

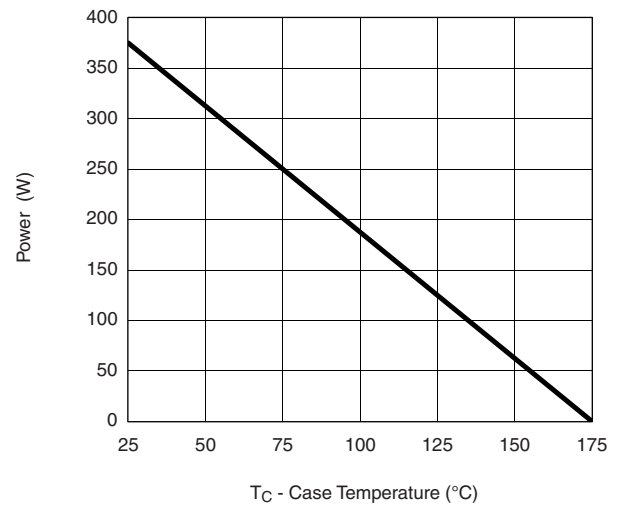


* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

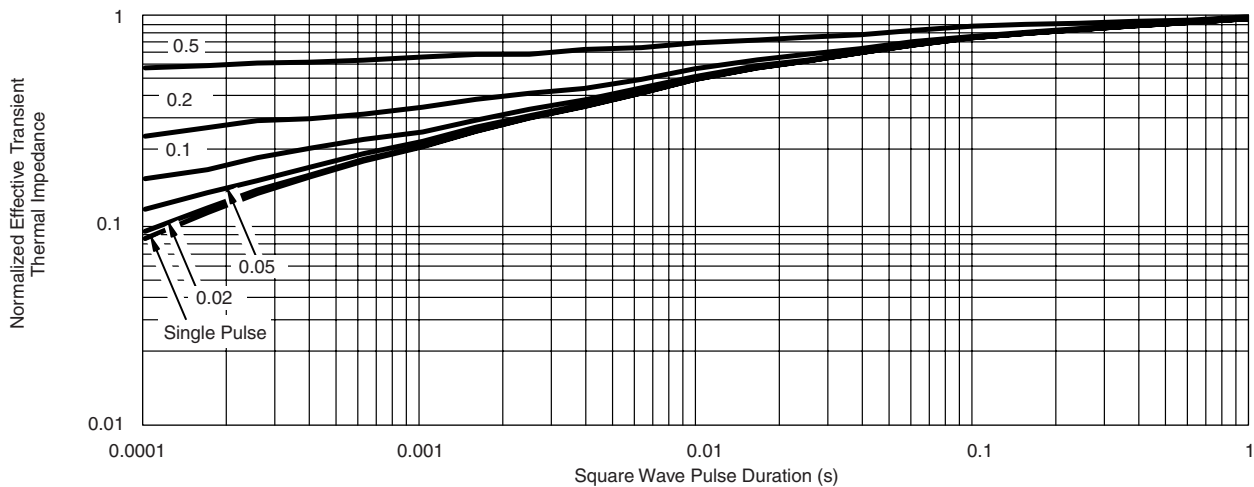
Safe Operating Area, Junction-to-Case

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


Max. Avalanche and Drain Current vs. Case Temperature*



Power Derating, Junction-to-Case

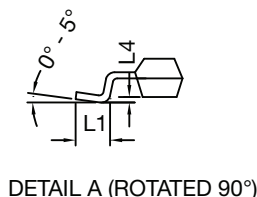


Normalized Thermal Transient Impedance, Junction-to-Case

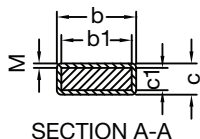
* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73493>.

TO-263 (D²PAK): 3-LEAD



DETAIL A (ROTATED 90°)



SECTION A-A

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.

DIM.		INCHES		MILLIMETERS	
		MIN.	MAX.	MIN.	MAX.
A		0.160	0.190	4.064	4.826
b		0.020	0.039	0.508	0.990
b1		0.020	0.035	0.508	0.889
b2		0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2		0.045	0.055	1.143	1.397
D		0.340	0.380	8.636	9.652
D1		0.220	0.240	5.588	6.096
D2		0.038	0.042	0.965	1.067
D3		0.045	0.055	1.143	1.397
D4		0.044	0.052	1.118	1.321
E		0.380	0.410	9.652	10.414
E1		0.245	-	6.223	-
E2		0.355	0.375	9.017	9.525
E3		0.072	0.078	1.829	1.981
e		0.100 BSC		2.54 BSC	
K		0.045	0.055	1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
M		-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

ECN: T13-0707-Rev. K, 30-Sep-13
DWG: 5843

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay:

[SUM110P04-05-E3](#)